



Romania and High Power Lasers Towards Extreme Light Infrastructure in Romania

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The Extreme Light Infrastructure





Contents



- GiWALAS laser facility
- TEWALAS laser facility
- CETAL project
- Extreme Light Infrastructure project



CLARK MXR Laser – CPA 2101 (2006)



Er:glass fiber oscillator, frequency doubled

- Laser wavelength: 1550 nm → 775nm
- Pulse duration ~200fsec
- Repetition rate: 35MHz
- Pulse energy ~43 pJ
- Average power ~1.5mW

Ti:sapphire regenerative amplifier

- Laser wavelength 775nm
- Pulse duration ~ 200 fsec
- Repetition rate 2kHz
- Maximum pulse energy ~ 700 µJ
- Average power ~ 1.4W





Femtosecond Laser and the Experimental Set-up for Micro-nanotechnologies (2007)





Laser wavelength, 775 nm; E_{pulse} = 0.7 mJ; t_p < 200 fs; f_{rep} = 2 kHz













TEWALAS Specifications



Laser specifications	Measured value
Central wavelength	808 nm
Spectral bandwidth	> 65 nm
Pulse energy before compressor	≤ 600 mJ
Pulse energy after compressor	≤ 450 mJ
Compressed pulse duration	25 ± 2 fs
Repetition rate	10 Hz
Pulse energy stabilization (RMS)	1.85%
Nanosecond pre-pulses contrast	8x10 ⁻⁸

2 - 10-5

ASE contract @1 no





- Pulse duration (spectral bandwidth, phase corrections)
- Intensity contrast (ASE, picosecond-nanosecond pre-pulses)

• Available focused intensity - Strehl ratio (high beam quality pump lasers, wavefront corrections with deformable mirrors)



Pulse spectrum narrowing during Ti:Sa amplification – TEWALAS





TEWALAS laser spectra: (a) without active Mazzler; (b) optimized by Mazzler. Mauve line – FEMTOLASERS oscillator (100 nm bandwidth); yellow line – after the first multi-pass amplifier, bandwidths - (a) 40 nm, (b) 75 nm; white line - after the second multi-pass amplifier- bandwidths (a) 35 nm, (b





Temporal distortion of the amplified re-compressed pulse is produced by:

- dispersion and phase distortions introduced by the laser amplifier system
- spectral gain narrowing in Ti:sapphire amplifiers



TEWALAS: Pulse duration measurements using SPIDER (a) with Dazzler phase correction; (b) without phase correction. All cases: with spectrum correction by Mazzler

Amplified spontaneous emission (ASE) and nanosecond intensity contrast





ASE contrast measured with a 3-rd order auto-correlator (SEQUOIA)

Measured intensity contrast: ASE < 10⁻⁹ Nanosecond @ 600mJ: 8x10⁻⁸







Micro/nano-technologies (low energy, high repetition rate):

- -Thin films micro-processing by femtosecond laser ablation
- Nano-processing in intensified laser field
- Direct laser writing of micro/nanostructures by two-photon photopolymerization
- Two-Photon Excited Spectroscopy

R&D based on femtosecond lasers (high energy):

- Multiple pulses generation in stretcher-compressor femtosecond laser systems
- Simulations and experiments of coherent beam combination
- Non-linear propagation of focused ultrashort pulses in air
- Theoretical studies of high intensity laser field matter interaction



Direct Laser Writing (DLW) Workstations



Microscope for 3D lithography and laser spectroscopy













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Next (possible) studies based on existing femtosecond lasers:

- Coherent combination of ultra-short pulses using interferometric methods
- X-ray generation using ultra-short laser pulses
- Collinear pump-probe experiments
- THz radiation generation
- Plasma mirror studies
- Study of absorption and density gradients in laser-produced plasmas
- Diagnosis and characterization of laser beams and optical components for nanosecond & femtosecond high energy lasers
- Large bandwidth OPCPA (OPCPA at critical wavelength degeneracy)



High power femtosecond laser projects:

• 1-PW (CETAL project, 2010-2013)

• 10-PW (Extreme Light Infrastructure, Romanian Pillar for Nuclear Physics

– ELI-RO-NP, 2010-2015)



ELI-NP building







Possible solutions for a 10-PW laser



A) OPCPA based laser system (910-nm central wavelength): Front-End \rightarrow very broad-band signal radiation at 910-nm central wavelength generated by chirp-compensated collinear OPA. High power OPCPA in large aperture DKDP crystals

E1) Hybrid laser system at ~ 800 nm central wavelength:

- Front-End based on OPCPA in nonlinear crystals (BBO, LBO)
- High energy amplification in Ti:sapphire crystals

Basic solution for ELI-RO-NP laser

B2) Ti:sapphire amplifiers at ~ 800 nm central wavelength :

or

- Front-End based on Ti:sapphire amplification
- High energy amplification in Ti:sapphire crystals

C) Hybrid laser system with Front-End based on OPCPA in BBO crystals and high energy amplification in mixed silicate/phosphate Nd-doped glasses near 1 µm wavelength

Alternative solution for ELI-RO-NP laser







Laser Architecture

ELI – RO Schematic Drawing







Overview of ELI-NP Multi-PW Laser







Overview of ELI-NP laser arm











- GIWALAS facility productive
- TEWALAS facility fully comissioned + productive
- CETAL PW laser system on the track
- Extreme Light Infrastructure feasibility study reviewed





Thank You for attention!

